



### 30V P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on) max</sub>	<b>Ι</b> <sub>D</sub> Τ <sub>A</sub> = 25°C
	$50m\Omega @ V_{GS} = -10V$	-3.7A
-30V	60mΩ @ V <sub>GS</sub> = -4.5V	-3.3A
	85mΩ @ $V_{GS}$ = -2.5V	-2.7A

## Description

This new generation Small-Signal enhancement mode MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

# Applications

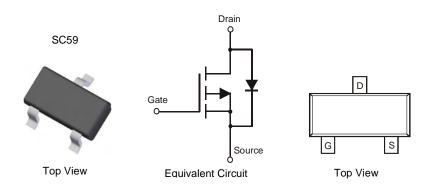
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

### Features

- Low Input Capacitance
- Low On-Resistance
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SC59
- Case Material: Molded Plastic "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
DMG3401LSN-7	SC59	3000/Tape & Reel

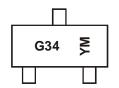
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



G34 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

#### Date Code Key

Date Code Rey												
Year	<b>201</b> <sup>2</sup>	1	2012		2013	20	14	2015		2016	2	2017
Code	Y		Z		А	E	3	С		D		E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage	V <sub>DSS</sub>	-30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±12	V		
Continuous Drain Current (Note 5) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	ID	-3.0 -2.3	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	Ι <sub>D</sub>	-3.7 -2.9	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)	I <sub>DM</sub>	-30	А		
Maximum Body Diode Continuous Current (Note 6)	I <sub>S</sub>	-1.5	А		

## **Thermal Characteristics**

Characteristic		Symbol	Value	Units	
Tatal Dowar Dissipation	(Note 5)	0	0.8	W	
Total Power Dissipation	(Note 6)	PD	1.2	VV	
Thermel Desistance, lunction to Ambient	(Note 5)	D	159		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ extsf{ heta}JA}$	105	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R <sub>θ</sub> JC	36		
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C	

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)				•	-	
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>	-	-	-1.0	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Body Leakage	IGSS	-	-	±100	nA	$V_{GS} = \pm 12V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-1.0	-1.3	V	$V_{DS} = V_{GS}, I_D = -250 \mu A$
		-	41	50		$V_{GS} = -10V, I_D = -4A$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	-	47	60	mΩ	$V_{GS} = -4.5V, I_D = -3.5A$
		-	60	85		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.5A
Forward Transfer Admittance	Y <sub>fs</sub>	-	12	-	S	$V_{DS} = -5V, I_D = -4A$
Diode Forward Voltage	V <sub>SD</sub>	-	-0.8	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C <sub>iss</sub>	-	1326	-		
Output Capacitance	Coss	-	103	-	pF	$V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>	-	71	-		
Gate Resistance	Rg	-	7.3	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	-	11.6	-		
Total Gate Charge (V <sub>GS</sub> = -10V)	Qq	-	25.1	-		
Gate-Source Charge	Q <sub>gs</sub>	-	2	-	nC	$V_{DD} = -15V, I_D = -4A$
Gate-Drain Charge	Q <sub>qd</sub>	-	1.7	-		
Turn-On Delay Time	t <sub>D(on)</sub>	-	8	-		
Turn-On Rise Time	tr	-	13	-		V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V,
Turn-Off Delay Time	t <sub>D(off)</sub>	-	71	-	nS	$R_{GEN} = 6\Omega, R_L = 3.75\Omega$
Turn-Off Fall Time	tf	-	38	-	1	

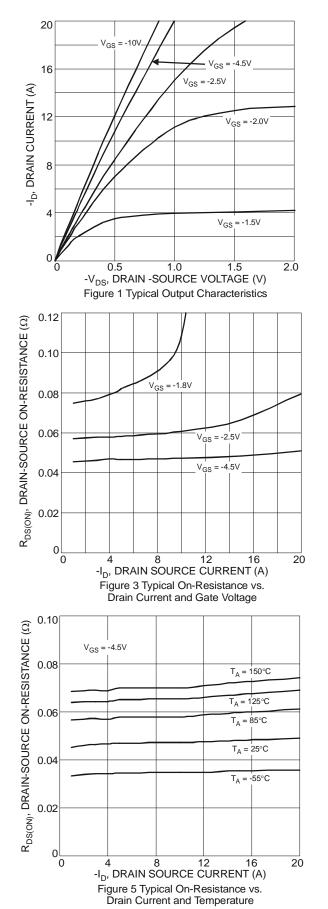
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

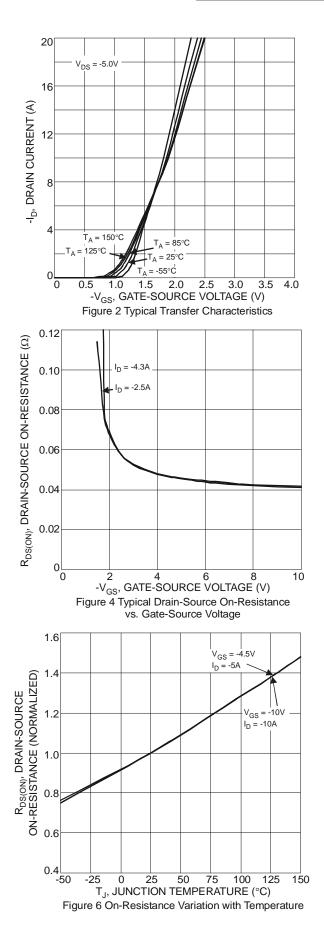
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout

Source duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing

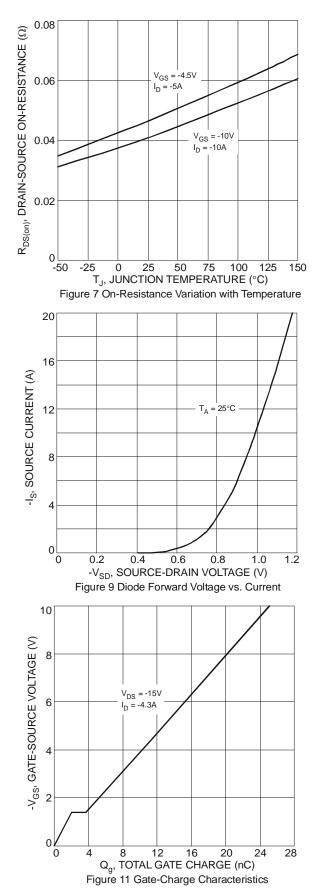
Notes:

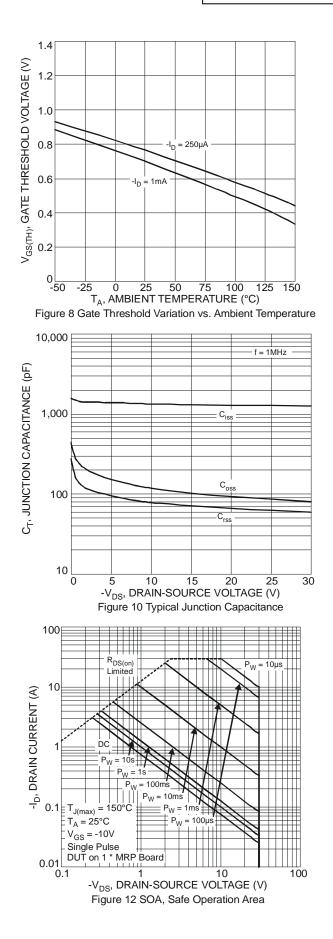




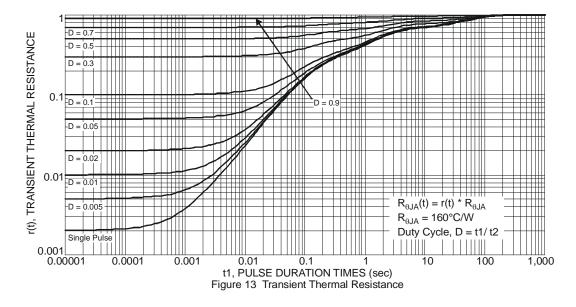






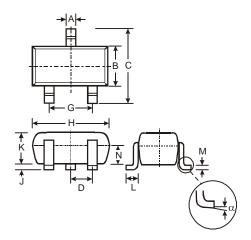






# **Package Outline Dimensions**

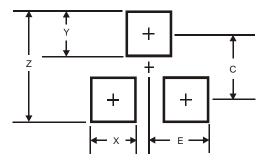
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



	SC59							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	-	-	0.95					
G	-	-	1.90					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
к	1.00	1.30	1.10					
L	0.35	0.55	0.40					
М	0.10	0.20	0.15					
Ν	0.70	0.80	0.75					
α	0°	8°	-					
All Dimensions in mm								

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.4
Х	0.8
Y	1.0
С	2.4
E	1.35



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